# GERMANIUM DIODE

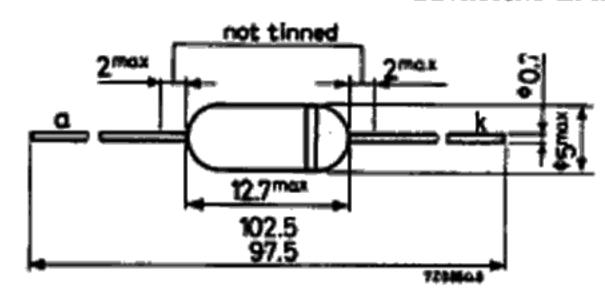
Germanium diode in all glass construction for use in a.m. detector circuits.

Type 2-OA79 consists of 2 diodes OA79 selected for operation in a ratio detector circuit.

### MECHANICAL DATA

Dimensions in mm

The white band indicates the cathode side



## RATINGS (Limiting values) 1)

Continuous reverse voltage	$v_R$	max.	30	ν
Repetitive peak reverse voltage	VRRM	max.	45	٧
Forward current (d.c.)	IF	max,	35	mΑ
Repetitive peak forward current	IFRM	max.	100	mΑ
Non repetitive peak forward current (t≤1 s)	IFSM	max.	200	mA
Operating ambient temperature	Tamb	-50 to	+60	°C

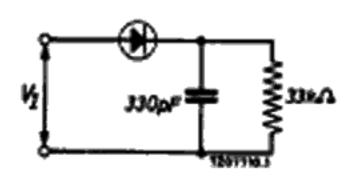
#### CHARACTERISTICS

Forward voltage		T <sub>amb</sub> = 25°C	T <sub>amb</sub> = 60 °C	_
I <sub>F</sub> = 0.1 mA	$v_{\mathbf{F}}$	typ. 0.23 0.15 to 0.30	typ. 0.16 0.1 to 0.25	v v
IF * 10 mA	$v_{\mathbf{F}}$	typ. 1.5 0.8 to 2.2	typ. 1.4 0.7 to 2.1	V V
IF = 30 mA	$v_{\mathbf{F}}$	typ. 2.8 1.4 to 4.0	typ. 2.6 1.2 to 3.8	v v
Reverse current				
V <sub>R</sub> = 0.1 V	$I_{\mathbf{R}}$	typ. 0.35 < 1.0	typ. 4.5 <	μΑ μΑ
V <sub>R</sub> = 1.5 V	$1_{\mathbf{R}}$	typ. 0.8 0.1 to 2.8	typ. 6 0.8 to 25	$\mu$ A $\mu$ A
VR = 10 V	$I_{\mathbf{R}}$	typ. 4.5 0.4 to 18	typ. 16 2.5 to 60	μ <b>Α</b> μ <b>Α</b>
v <sub>R</sub> = 30 v	$I_{\mathbb{R}}$	typ. 35 1.5 to 150	typ. 60 60 to 300	μ <b>Α</b> . μ <b>Α</b>
V <sub>R</sub> = 45 V	$I_{\mathbf{R}}$	typ. 90 4 to 350	typ. 170 15 to 500	μA μA

<sup>1)</sup> Limiting values according to the Absolute Maximum System as defined in IEC publication 134.
7Z3 1247

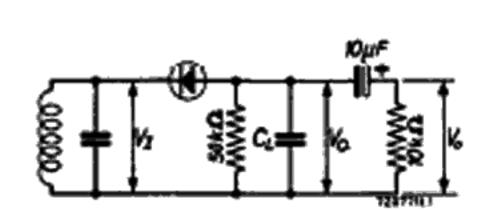
## APPLICATION INFORMATION

Measuring circuit at Tamb = 25 °C



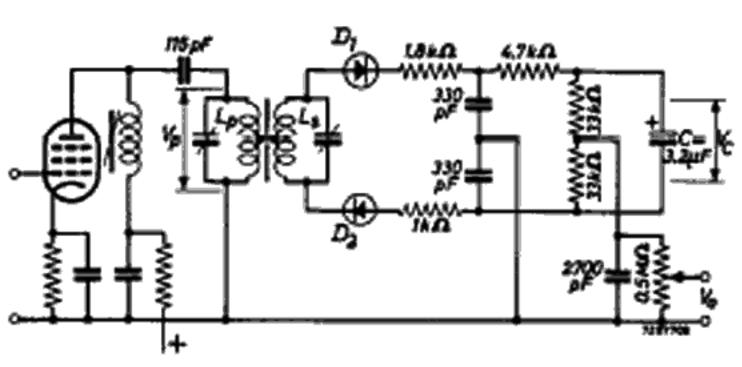
$$V_{I(RMS)}$$
 = 3 V η typ. 85 %  
f = 10.7 MHz  $R_{d}$  typ. 15 kΩ  $R_{d}$  13.5 to 19 kΩ

Diode in an a.m. detector circuit at Tamb = 25 °C



$$V_{I(RMS)} = 0.1 \text{ V} \quad V_{O} \quad \text{typ. 55 mV}$$
  
 $f = 0.5 \text{ MHz } V_{O(rms)} \quad \text{typ. 4.5 mV}^{1}$   
 $R \quad \text{typ. 40 kt.}^{2}$ 

## Matched pair in a ratio detector circuit



$$L_p = 7.4 \mu H$$
 $Q_0 = 80 \text{ unloaded}$ 
 $R = 40 \text{ k}\Omega \text{ unloaded}$ 
 $Tap = 0.5$ 
 $L_s = 4.4 \mu H$ 
 $Q_0 = 150 \text{ unloaded}$ 
 $R = 45 \text{ k}\Omega \text{ unloaded}$ 
 $kQ = 0.83$ )
 $f_0 = 10.7 \text{ MHz}$ 
 $\Delta f = 15 \text{ kHz}$ 
 $m = 0.3$ 

a.m. suppression factor at  $V_C = 2$  to 20.V

$$f = f_0$$

$$f = f_0 \pm 25 \text{ kHz}$$

$$\alpha \geq 15$$

For optimum a.m. suppression D<sub>1</sub> must be that diode of the matched pair which has the better dynamic forward characteristic.

# For new design the successor types AA119; 2-AA119 are recommended

 $<sup>\</sup>frac{1}{2}$ ) Modulation factor m = 0.3

<sup>2)</sup> Modulation factor m = 0

<sup>3)</sup> Measured in the circuit with  $V_p = 350 \text{ mV}$